

ISC Silicon NPN Power Transistor

DESCRIPTION

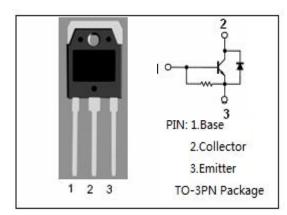
- · High Breakdown Voltage-
 - : V_{CBO}= 1500V (Min)
- · High Switching Speed
- Built-in Damper Diode
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

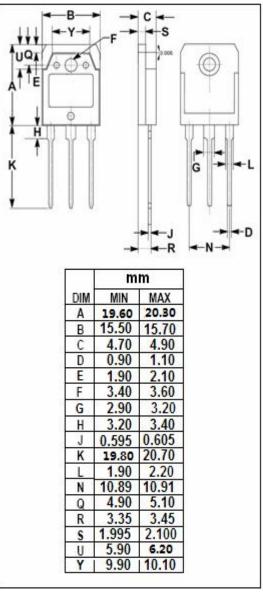
APPLICATIONS

• Designed for horizontal deflection output applications.



SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	1500	V
V _{CES}	Collector-Emitter Voltage	1500	V
V _{EBO}	Emitter-Base Voltage	5	V
lc	Collector Current- Continuous	4	Α
Іср	Collector Current-Peak	15	Α
Івр	Base Current-Peak	3.5	Α
P _C	Collector Power Dissipation @ T _a = 25℃	2.5 W	
	Collector Power Dissipation @ T _C = 25 °C	70	v v
TJ	Junction Temperature 130		$^{\circ}$ C
T _{stg}	Storage Temperature Range -55~130		$^{\circ}$







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2SD1441

ELECTRICAL CHARACTERISTICS

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 200mA; I _C = 0	5			V
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C = 3A; I _B = 1A			1.0	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	I _C = 3A; I _B = 1A			1.5	V
І _{СВО}	Collector Cutoff Current	V _{CB} = 750V; I _E = 0 V _{CB} = 1500V; I _E = 0			50 1.0	μA mA
h _{FE}	DC Current Gain	I _C = 3A; V _{CE} = 10V	5		15	
f⊤	Current-Gain—Bandwidth Product	I _C = 0.5A; V _{CE} = 10V		2		MHz
V _{ECF}	C-E Diode Forward Voltage	I _F = 4A			2.2	V
t _s	Storage Time	Ic= 3A, I _{Bend} = 1A, L _{leak} = 5 μ Н			9.0	μ s
t _f	Fall Time	IC- OA, IBenα- IA, Lleak- S μ Π			0.75	μ s

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